## IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A method of producing an alumina film mainly in  $[\alpha]$  alpha crystal structure, characterized in that in forming the alumina film mainly in  $\alpha$  erystal structure on a substrate (including a substrate having a film previously formed thereon), comprising:

treating the surface of the substrate is treated with a ceramic powder mainly having the a crystal structure which is the same as that of alumina in the  $[\alpha]$  alpha crystal structure to form fine scratches on the surface of the substrate; and then

forming the alumina film mainly in alpha crystal structure on the substrate.

Claim 2 (Currently Amended): The method of producing an the alumina film according to Claim 1, wherein the ceramic powder used is an alumina powder in  $[[\alpha]]$  alpha crystal structure.

Claim 3 (Currently Amended): The method of producing an the alumina film according to Claim 2, wherein the alumina powder used has an average particle diameter of  $50 \mu m$  or less.

Claim 4 (Currently Amended): The method of producing an the alumina film according to Claim 1, wherein the substrate used has a film formed on the surface thereof made of one or more compounds selected from the group consisting of compounds of one or more elements selected from the group consisting of elements in Groups 4a, 5a and 6a in the periodic table, Al, Si and Y with one or more elements of C, N, B, and O; the solid solutions thereof; and compounds of one or more elements of C, N, and B.

Claim 5 (Currently Amended): The method of producing an the alumina film according to Claim 4, wherein the substrate used has a hard film formed on the surface thereof containing comprising one or more compounds selected from the group consisting of TiN, TiC, TiCN, TiAlN and TiAlCrN.

Claim 6 (Currently Amended): The method of producing an the alumina film according to Claim 1, wherein treating the substrate surface treatment includes comprises a step of polishing the substrate surface with the ceramic powder.

Claim 7 (Currently Amended): The method of producing an the alumina film according to Claim 1, wherein treating the substrate surface treatment includes comprises a step of immersing and ultrasonicating the substrate in a liquid in which the ceramic powder is dispersed.

Claim 8 (Currently Amended): The method of producing an the alumina film according to Claim 1, wherein forming the alumina film is formed by comprises a gas-phase growth method.

Claim 9 (Currently Amended): The method of producing an the alumina film according to Claim 8, wherein the gas-phase growth method used is a method selected from the group consisting of CVD, PE-CVD, sputtering, ion plating and vapor deposition.

Claim 10 (Currently Amended): A method of producing a laminated film-coated part, eharacterized in that comprising forming an alumina film mainly in  $[\alpha]$  alpha crystal

structure is formed on the film previously formed on the substrate by using the method according to Claim 1.

Claim 11 (Currently Amended): A method of producing a laminated film-coated part comprising an alumina film namely in alpha crystal structure, characterized by including comprising: a step of forming a hard film containing one or more compounds selected from the group consisting of TiN, TiC, TiCN, TiAlN and TiAlCrN on a substrate, a step of treating the substrate a surface of the hard film with a ceramic powder mainly having [[the]] a crystal structure which is the same as that of alumina in the [[\alpha]] alpha crystal structure to form fine scratches on the surface of the hard film, and a step of forming an alumina film mainly in [[\alpha]] alpha crystal structure on the hard film substrate after the surface treatment with said ceramic powder, wherein the processing is performed in that order.

Claim 12 (New): The method of producing the alumina film according to Claim 1, further comprising washing the surface of the substrate subsequent to treating the substrate surface with the ceramic powder.

Claim 13 (New): The method of producing the alumina film according to Claim 1, comprising forming the alumina film mainly in alpha crystal structure at a temperature of 650 to 800°C.

Claim 14 (New): The method of producing the alumina film according to Claim 1, further comprising oxidizing the substrate at a temperature of 650 to 800°C prior to forming the alumina film on the substrate.

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Claim 15 (New): The method of producing the alumina film according to Claim 2, wherein the alumina powder has an average particle diameter of 1  $\mu$ m or less.

Claim 16 (New): The method of producing the alumina film according to Claim 1, wherein the thickness of the alumina film is in a range of 0.1  $\mu$ m to 20  $\mu$ m.

Claim 17 (New): The method of producing an alumina film according to Claim 1, wherein the thickness of the alumina film is in a range of 1  $\mu$ m to 5  $\mu$ m.